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GROUP 1700

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: WON-SUNG CHOI )  
Application No: 09/726,977 ) Group Art Unit 1763  
Filed: November 30, 2000 )  
For: THIN FILM DEPOSITION APPARATUS ) Examiner:  
FOR SEMICONDUCTOR ) Kackar, Ram N.

Commissioner for Patents  
Alexandria, VA 22313-1450

## AMENDMENT UNDER 37 C.F.R. §1.111

# 12C  
5/23/03  
mw

Sir:

In response to the Office Action dated February 26, 2003, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel claims 3, 15 and 16, without prejudice.

Please replace claims 1, 2, 6-9 and 13 with the following claims rewritten in "clean"

format:

1. (Three Times Amended) A semiconductor thin film deposition apparatus comprising:

- a reactor in which a wafer is received;
- a reaction gas supply unit for providing reaction gas to the reactor;
- an inert gas supply unit for providing inert gas to the reactor;
- an exhaust pump for exhausting gas from the reactor;
- an ozone generator for generating ozone to react with the reaction gas;
- a first ozone transfer unit having a first mass flow controller connected to the ozone generator, for receiving the ozone from the ozone generator to provide the reactor with a first ozone flow at a first flow rate for a thin film deposition on the wafer, wherein the first ozone flow and the reaction gas are provided into the reactor at respective times different from each other;